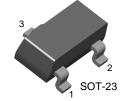


KSR1104

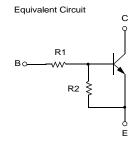
Switching Application (Bias Resistor Built In)

- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R₁ =47K Ω , R₂=47K Ω)
- Complement to KSR2104



1. Base 2. Emitter 3. Collector





NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current	100	mA
P _C	Collector Power Dissipation	200	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_a =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C}=10\mu A, I_{E}=0$	50			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =100μA, I _B =0	50			V
I _{CBO}	Collector Cut-off Current	V_{CB} =40V, I_{E} =0			0.1	μΑ
h _{FE}	DC Current Gain	V _{CE} =5V, I _C =5mA	68			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =10mA, I _B =0.5mA			0.3	V
f _T	Current Gain-Bandwidth Product	V _{CE} =10V, I _C =5mA		250		MHz
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0 f=1.0MHz		3.7		pF
V _I (off)	Input Off Voltage	$V_{CE}=5V, I_{C}=100\mu A$	0.5			V
V _I (on)	Input On Voltage	V_{CE} =0.3V, I_{C} =2mA			3	V
R ₁	Input Resistor		32	47	62	ΚΩ
R ₁ /R ₂	Resistor Ratio		0.9	1	1.1	

Typical Characteristics

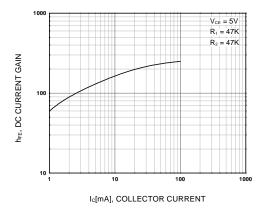


Figure 1. DC current Gain

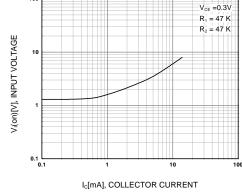


Figure 2. Input On Voltage

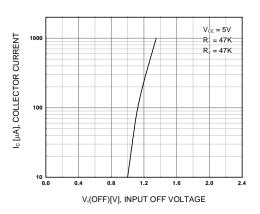


Figure 3. Input Off Voltage

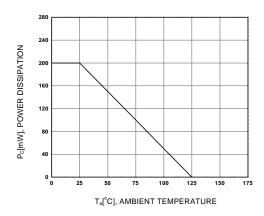
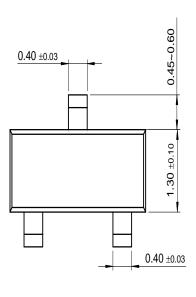
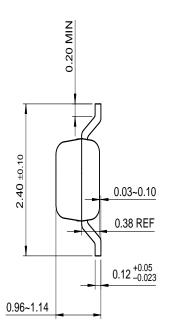


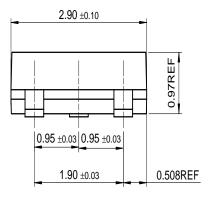
Figure 4. Power Derating

Package Dimensions

SOT-23







Dimensions in Millimeters

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FACT™	ImpliedDisconnect™	PACMAN™	SPM™
ActiveArray™	FACT Quiet series™	ISOPLANAR™	POP™	Stealth™
Bottomless™	FAST [®]	LittleFET™	Power247™	SuperSOT™-3
CoolFET™	FASTr™	MicroFET™	PowerTrench [®]	SuperSOT™-6
$CROSSVOLT^{TM}$	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E ² CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I^2C^{TM}	OCX^{TM}	RapidConfigure™	UHC™
Across the board.	Around the world.™	OCXPro™	RapidConnect™	UltraFET [®]
The Power Franchise™		OPTOLOGIC [®]	SILENT SWITCHER®	VCX TM
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Search:

Go

DATASHEETS, SAMPLES, BUY

TECHNICAL INFORMATION APPLICATIONS DESIGN CENTER SUPPORT COMPANY INVESTORS MY F.

Home >> Find products >>

KSR1104

NPN Epitaxial Silicon Transistor

Contents

- Features
- Product status/pricing/packaging
- Order Samples
- Qualification Support

Features

Switching Application (Bias Resister Built In)

- Switchng circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R₁=47KΩ, R₂=47KΩ)
- Complement to KSR2104

back to top

Product status/pricing/packaging

BUY

BUY

Datasheet Download this datasheet



e-mail this datasheet



This page Print version

Related Links

Request samples

How to order products

Product Change Notices (PCNs)

Support

Sales support

Quality and reliability

Design center

Product	Product status	Pb-free Status	Package type	Leads	Packing method
KSR1104MTF	Lifetime Buy	Ø	<u>SOT-23</u>	3	TAPE REEL
KSR1104MTF_NL	Lifetime Buy	Ø	<u>SOT-23</u>	3	TAPE REEL

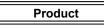


Indicates product with Pb-free second-level interconnect. For more information click here.

back to top

Qualification Support

Click on a product for detailed qualification data





back to top

© 2007 Fairchild Semiconductor



Products | Design Center | Support | Company News | Investors | My Fairchild | Contact Us | Site Index | Privacy Policy | Site Terms & Conditions | Standard Terms & Conditions |